Method of growing thin film electroluminescent structures

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Abstract

The present invention concerns a method of growing a cerium-doped SrS phosphor layer by the Atomic Layer Epitaxy-method. According to the invention an organometallic cerium compound containing at least one cyclopentadienyl type ligand is used as a precursor for the dopant cerium. The cyclopentadienyl type cerium compounds can be used as ALE precursors at about 400 C. substrate temperatures without any observable thermal decomposition during processing